

# CD4148WTP

## SMALL SIGNAL DIODE

VOLTAGE: 75V

CURRENT: 150mA

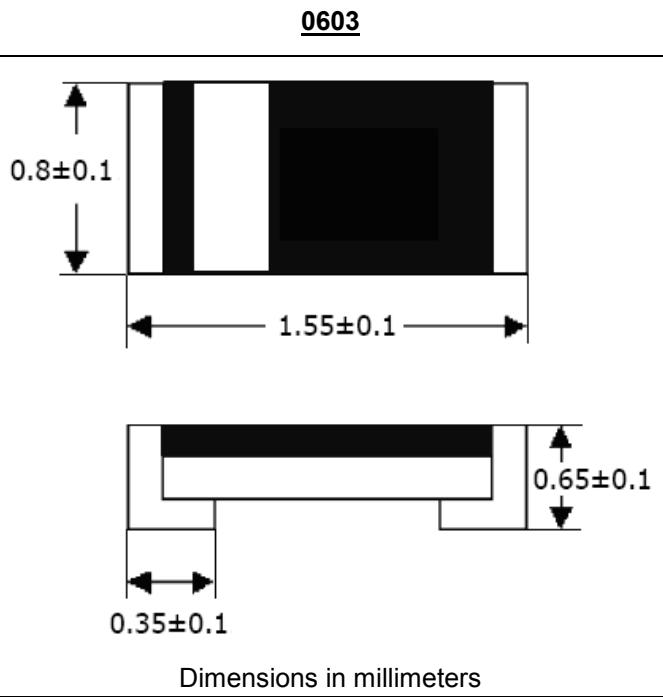


### FEATURE

Silicon epitaxial planar diode  
SMD chip pattern, available in various dimension included  
0805 & 0603  
Leadfree and RoHS compliance components

### MECHANICAL DATA

Size: 1206  
Weight: approx. 0.01g  
Marking: cathode terminal



0603

Dimensions in millimeters

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

Parameter	Symbol	Limit	units
Reverse Voltage	V <sub>r</sub>	75	V
Peak Reverse Voltage	V <sub>rm</sub>	100	V
Forward Continuous Current	I <sub>f(m)</sub>	300	mA
Average Rectified Current sin half wave rectification with resistive load $f \geq 50\text{Hz}$ (Note 1)	I <sub>f(av)</sub>	150	mA
Surge Forward Current at $t < 1\text{s}$ and $T_j = 25^\circ\text{C}$	I <sub>fsm</sub>	500	mA
Power dissipation (Note 1)	P <sub>tot</sub>	400	mW
Typical Thermal Resistance (Note 1)	θ <sub>th(ja)</sub>	375	°C/W
Junction Temperature	T <sub>j</sub>	175	°C
Storage Temperature	T <sub>stg</sub>	-65 ~ +175	°C

Note:

1. Valid provide that electrodes are kept at ambient temperature

Electrical Characteristics(TJ = 25 °C unless otherwise noted)

parameter	symbol	Test Condition	min	typ	max	unit
Forward Voltage	Vf	If=10mA			1.0V	V
Leakage Current	Ir	Vr=20V Vr=75V Vr=20V,Tj=150°C			25 5.0 50	nA uA uA
Capacitance	Ctot	Vf=Vr=0V			4	pF
Voltage Rise when Switching ON (tested with 50mA Pulses)	Vfr	Tp=0.1uS,Rise Time<30nS Fp=5 to 100KHZ			2.5	nS
Reverse Recovery Time	Trr	If=10mA,Ir=1 mA Vr=6v,Rl=100 Ω			4	nS
Rectification efficiency	η r	F=100MHz,VRF=2V	45			%

#### Rectification Efficiency Measurement Circuit

